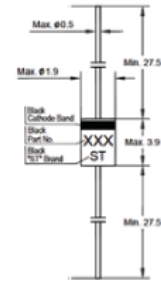


## Silicon Epitaxial Planar Switching Diode

### Applications

- High-speed switching

This diode is also available in MiniMELF case with the type designation LL4448.



Glass Case DO-35  
Dimensions in mm

### Absolute Maximum Ratings ( $T_a = 25^\circ\text{C}$ )

| Parameter                          | Symbol      | Value             | Unit             |
|------------------------------------|-------------|-------------------|------------------|
| Peak Reverse Voltage               | $V_{RM}$    | 100               | V                |
| Reverse Voltage                    | $V_R$       | 75                | V                |
| Average Rectified Forward Current  | $I_{F(AV)}$ | 150               | mA               |
| Surge Forward Current at $t < 1$ s | $I_{FSM}$   | 500               | mA               |
| Power Dissipation                  | $P_{tot}$   | 500 <sup>1)</sup> | mW               |
| Junction Temperature               | $T_j$       | 200               | $^\circ\text{C}$ |
| Storage Temperature Range          | $T_{stg}$   | - 65 to + 200     | $^\circ\text{C}$ |

<sup>1)</sup> Valid provided that leads at a distance of 8 mm from case are kept at ambient temperature.

### Characteristics at $T_a = 25^\circ\text{C}$

| Parameter                                                                                                   | Symbol                  | Min.        | Max.          | Unit                                 |
|-------------------------------------------------------------------------------------------------------------|-------------------------|-------------|---------------|--------------------------------------|
| Forward Voltage<br>at $I_F = 5$ mA<br>at $I_F = 100$ mA                                                     | $V_F$                   | 0.62<br>-   | 0.72<br>1     | V                                    |
| Reverse Leakage Current<br>at $V_R = 20$ V<br>at $V_R = 75$ V<br>at $V_R = 20$ V, $T_j = 150^\circ\text{C}$ | $I_R$<br>$I_R$<br>$I_R$ | -<br>-<br>- | 25<br>5<br>50 | nA<br>$\mu\text{A}$<br>$\mu\text{A}$ |
| Reverse Breakdown Voltage<br>at $I_R = 100$ $\mu\text{A}$                                                   | $V_{(BR)R}$             | 100         | -             | V                                    |
| Capacitance<br>at $V_R = 0$ , $f = 1$ MHz                                                                   | $C_{tot}$               | -           | 4             | pF                                   |
| Reverse Recovery Time<br>at $I_F = 10$ mA to $I_R = 1$ mA, $V_R = 6$ V, $R_L = 100$ $\Omega$                | $t_{rr}$                | -           | 4             | ns                                   |

